

Dr. Mikhail Glazov

leading researcher, Corresponding Member of Russian Academy of Science

Affiliation: **Ioffe Institute**, Polytechnicheskaya 26, 194021 St.Petersburg, Russia

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Personal details: Born June 8, 1982 in Leningrad, USSR

Education: Graduated from St.-Petersburg State Polytechnical University, 2005

Master of Physics thesis (with honor):
"Effect of electron-electron interaction on spin relaxation in semiconductors"

PhD thesis (2008): "Spin dynamics of electrons and excitons in quantum wells and quantum dots"

Habilitation (Dr. Sci.) thesis (2012): "Spin and kinetic phenomena in nanostructures and graphene"

Research interests: Semiconductor theory, two-dimensional materials,
spin effects, light-matter coupling effects

Research activity: over 120 publications, over 2000 citations, h-index is 26

Languages: Russian – native, English – fluent, French – basic, Italian – beginner

Teaching: 2005 – 2009, practical training of undergraduate
students on Calculus in St. Petersburg State Polytechnical University
since 2010 courses "Spin phenomena in semiconductors", "Physics of low dimensional structures"
at Academic University (professor since 2013), St. Petersburg

Management/administrative tasks: since 2005, Referee for the international journals
Nature, Science, Physical Review, Physical Review Letters, etc.
and several Russian journals in Condensed Matter Physics
Principal investigator of RFBR and RAS funded projects

Member of Scientific Council on Semiconductor Physics of RAS

Member of program committee of the Russian Conference on Semiconductor Physics (since 2015)

Expert of RAS

AWARDS

Dynasty Foundation Scholarship for undergraduate students (2003 – 2005)

A. F. Ioffe Institute Young Scientist Award (2003)

A. F. Ioffe Institute Prize in 2004 (together with E.L. Ivchenko), in 2005 (together with V.I. Perel', S.A. Tarasenko, and I.N. Yassievich), in 2008 (together with L.E. Golub), in 2010 (together with E.L. Ivchenko, D.R. Yakovlev, and M. Bayer), in 2011 (together with T.V. Shubina and A.A. Toropov), in 2014 (together with S.A. Tarasenko and E.L. Ivchenko)

Dynasty Foundation Scholarship for PhD students (2006 – 2008)

Medal “For devotion to science” #252 (2007)

The best talk on VIII Russian Conference on Semiconductor Physics (2007)

Dynasty Foundation Scholarship for PostDocs (2009 – 2011)

President Grant for Young Scientists (2009, 2015, 2017)

Young Scientist Award by Foundation for Support of Education and Research (2012)

Medal of Russian Academy of Sciences and Prize for Young Researchers (2014)

Dynasty Foundation Scholarship for Young Professors (2015)

Euler prize by St.-Petersburg Government and St.-Petersburg scientific center of RAS (2015)

Professor of the Russian Academy of Science (2016)

Corresponding Member of the Russian Academy of Science (2016)

APS Outstanding Referees (2018)

SELECTED PUBLICATIONS

1. M.M. Glazov and E.L. Ivchenko, Precession Spin Relaxation Mechanism Caused by Frequent Electron-Electron Collisions. JETP Lett. **75**, 403 (2002).
2. M.M. Glazov, Coherent spin dynamics of electrons and excitons in nanostructures (a review), Physics of the Solid State **54**, 1 (2012).
3. E. A. Chekhovich, M. M. Glazov, A. B. Krysa, M. Hopkinson, P. Senellart, A. Lemaître, M. S. Skolnick, and A. I. Tartakovskii, Element-sensitive measurement of the hole-nuclear spin interaction in quantum dots, Nat. Phys. **9**, 74 (2013).
4. M.M. Glazov, S.D. Ganichev, High frequency electric field induced nonlinear effects in graphene, Physics Reports **535**, 101-138 (2014).
5. M. M. Glazov, T. Amand, X. Marie, D. Lagarde, L. Bouet, and B. Urbaszek, Exciton fine structure and spin decoherence in monolayers of transition metal dichalcogenides Phys. Rev. B **89**, 201302(R) (2014).
6. M. Manca, M. M. Glazov, C. Robert, F. Cadiz, T. Taniguchi, K. Watanabe, E. Courtade, T. Amand, P. Renucci, X. Marie, G. Wang, B. Urbaszek, Enabling valley selective exciton scattering in monolayer WSe₂ through upconversion, Nature Communications **8**, 14927 (2017).